

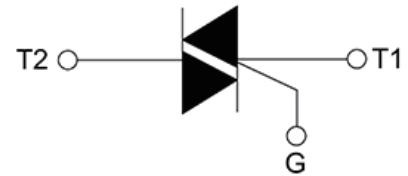
DESCRIPTION:

The chip triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. The chip embeds a TVS structure to absorb the inductive turn-off energy such as those described in the IEC 61000-4-5 standards. At the same time, the triac shields the positive signal trigger to reduce the probability of product misoperation. It is triggered with a negative gate current flowing out of the gate



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	16	A
V_{DRM}/V_{RRM}	600	V
$I_{GT\ I/II/III}$	10/10/10	mA



ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-150	°C
Repetitive peak off-state voltage ($T_j=25^{\circ}C$)	V_{DRM}	600	V
Repetitive peak reverse voltage ($T_j=25^{\circ}C$)	V_{RRM}	600	V
RMS on-state current ($T_c \leq 125^{\circ}C$)	$I_{T(RMS)}$	16	A
Non repetitive surge peak on-state current (full cycle , $t_p=20ms$, $T_j=25^{\circ}C$)	I_{TSM}	160	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6ms$, $T_j=25^{\circ}C$)		176	
I^2t value for fusing ($t_p=10ms$, $T_j=25^{\circ}C$)	I^2t	128	A^2s
Critical rate of rise of on-state current ($I_G=2 \times I_{GT}$, $f=100Hz$, $T_j=150^{\circ}C$)	di/dt	100	$A/\mu s$
Peak gate current ($t_p=20\mu s$, $T_j=150^{\circ}C$)	I_{GM}	4	A
Average gate power dissipation ($T_j=150^{\circ}C$)	$P_{G(AV)}$	1	W

Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^{\circ}\text{C}$; non-repetitive, off-state; FIG)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V}$ $R_L=33\Omega$	I - II -III	MAX.	10	mA
V_{GT}		I - II -III	MAX.	1	V
V_{GD}	$V_D=V_{DRM}$ $T_j=150^{\circ}\text{C}$ $R_L=3.3\text{k}\Omega$	I - II -III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I -III	MAX.	20	mA
		II		35	
I_H	$I_T=500\text{mA}$		MAX.	20	mA
dV/dt	$V_D=400\text{V}$ Gate Open $T_j=150^{\circ}\text{C}$		MIN.	200	V/ μs
$(dI/dt)_c$	$(dV/dt)_c=20\text{V}/\mu\text{s}$, $T_j=150^{\circ}\text{C}$		MIN.	1.8	A/ms
t_{on}	$I_G=20\text{mA}$ $I_A=200\text{mA}$ $I_R=20\text{mA}$ $T_j=25^{\circ}\text{C}$		TYP.	2.5	μs
t_{off}				25	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=22.5\text{A}$ $t_p=380\mu\text{s}$	$T_j=25^{\circ}\text{C}$	1.4	V
V_{TO}	Threshold voltage	$T_j=150^{\circ}\text{C}$	0.75	V
R_D	Dynamic resistance	$T_j=150^{\circ}\text{C}$	27	$\text{m}\Omega$
I_{DRM}	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^{\circ}\text{C}$	5	μA
I_{RRM}		$T_j=150^{\circ}\text{C}$	1.5	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.2	$^{\circ}\text{C}/\text{W}$
$R_{th(j-a)}$	junction to ambient (AC, in free air, $S=2\text{cm}^2$)	45	$^{\circ}\text{C}/\text{W}$

FIG : Maximum power dissipation versus RMS on-state current

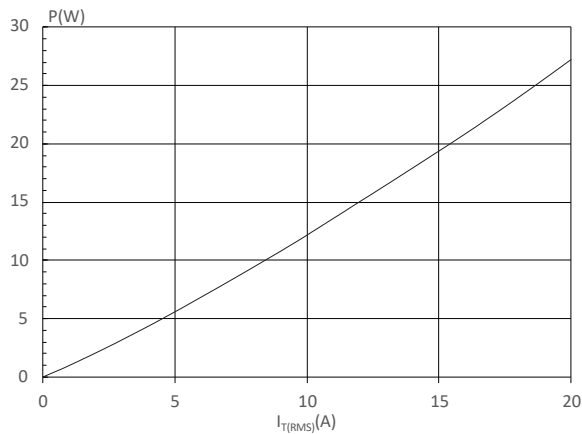


FIG : RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35 μ m)(full cycle)

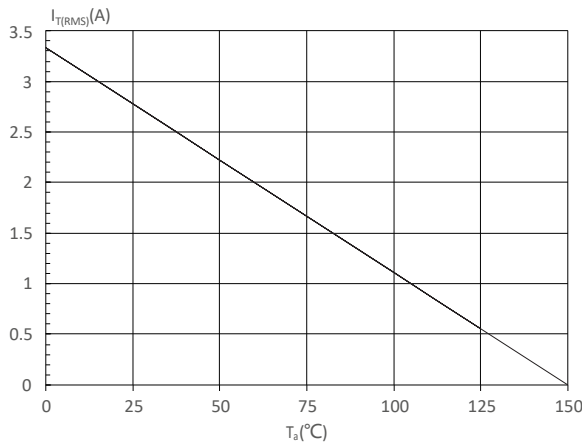


FIG : On-state characteristics

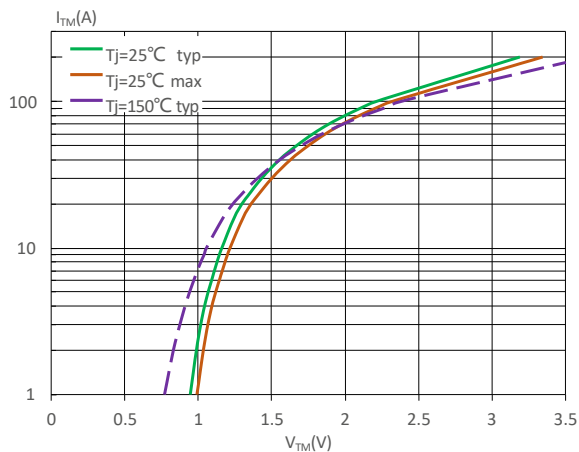


FIG : RMS on-state current versus case temperature

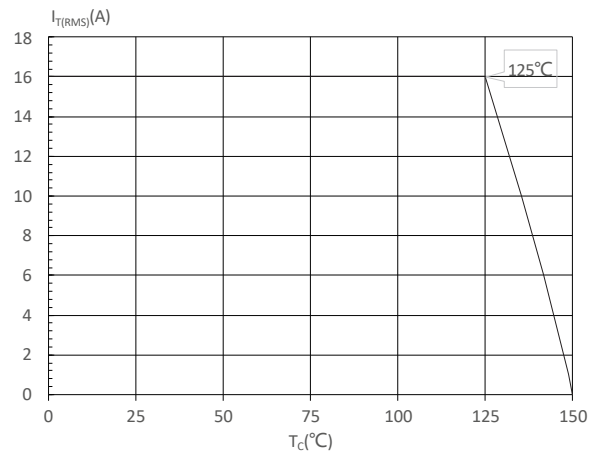


FIG : Surge peak on-state current versus number of cycles

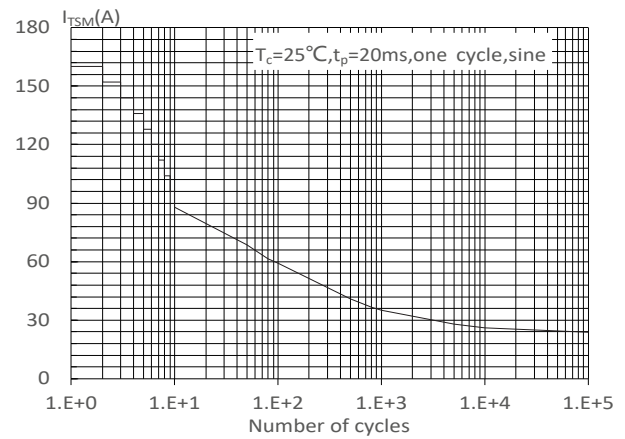


FIG : Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 20ms$, and corresponding value of I^2t ($di/dt < 100A/\mu s$)

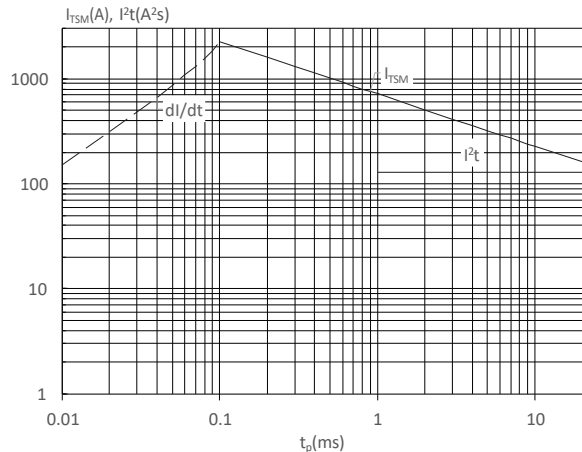


FIG : Relative variations of gate trigger current, holding current and latching current versus junction temperature

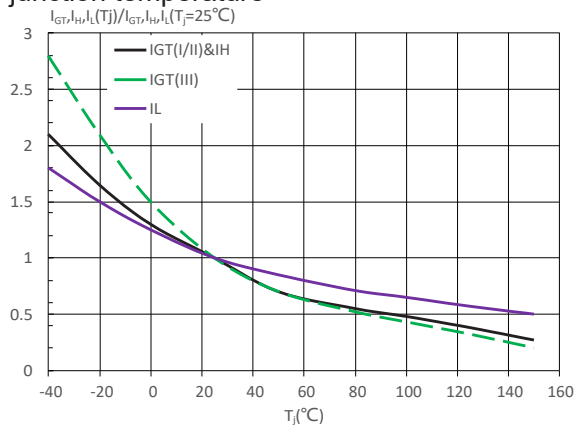
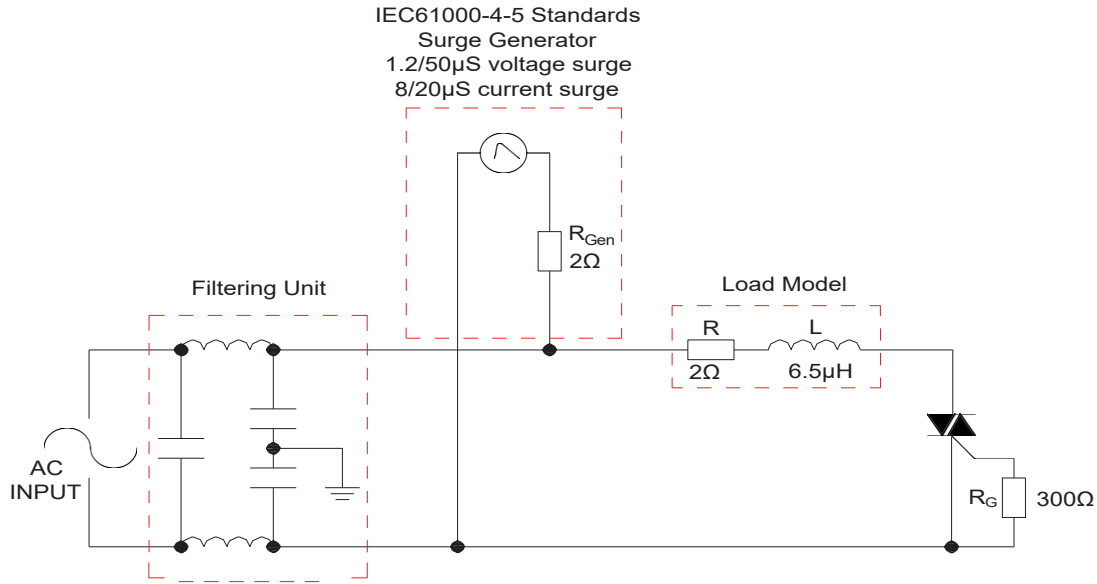


FIG : Test circuit for inductive and resistive loads to IEC-61000-4-5 standards


SOLDERING PARAMETERS

Reflow Condition		Pb-Free assembly (see figure at right)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150 $^{\circ}$ C
	-Temperature Max($T_{s(max)}$)	+200 $^{\circ}$ C
	-Time (Min to Max) (t_s)	60-180 secs.
Average ramp up rate (Liquidus Temp (T_L) to peak)		3 $^{\circ}$ C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3 $^{\circ}$ C/sec. Max
Reflow	-Temperature(T_L)(Liquidus)	+217 $^{\circ}$ C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_p)		+260(+0/-5) $^{\circ}$ C
Time within 5 $^{\circ}$ C of actual Peak Temp (t_p)		20-40secs.
Ramp-down Rate		6 $^{\circ}$ C/sec. Max
Time 25 $^{\circ}$ C to Peak Temp (T_p)		8 min. Max
Do not exceed		+260 $^{\circ}$ C

